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Transistor

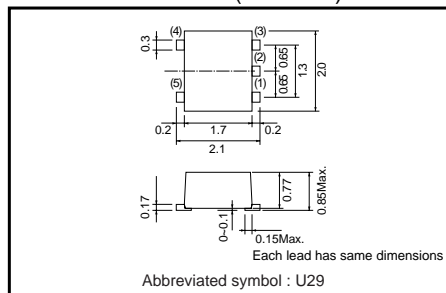
Small switching (−20V, −1.5A)

US5U29

●Features

- 1) The US5U29 combines Pch MOSFET with a Schottky barrier diode in a single TSMT5 package.
- 2) Pch MOSFET have a low on-state resistance with a fast switching.
- 3) Pch MOSFET is reacted a low voltage drive(2.5V)
- 4) The Independently connected Schottky barrier diode have a low forward voltate.

●External dimensions (Unit : mm)



●Applications

Load switch, DC/DC conversion

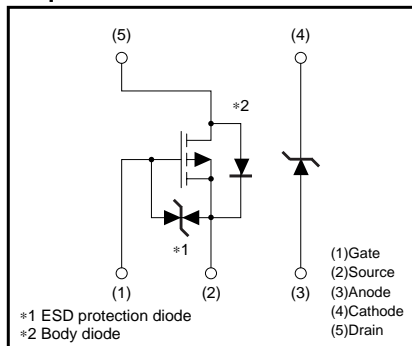
●Structure

Silicon P-channel MOSFET
 Schottky Barrier DIODE

●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
US5U29		○

●Equivalent circuit



●Absolute maximum ratings (Ta=25°C)

< MOSFET >

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	−20	V
Gate-source voltage	V _{GSS}	±12	V
Drain current	Continuous	I _D	±1 A
	Pulsed	I _{DP}	±4 A PW≤10μs DUTY CYCLE ≤1%
Source current (Body diode)	Continuous	I _S	−0.4 A
	Pulsed	I _{SP}	−4 A PW≤10μs DUTY CYCLE ≤1%
Channel temperature	T _{ch}	150	°C

< Di >

Repetitive peak reverse voltage	V _{RM}	25	V
Reverse voltage	V _R	20	V
Forward current	I _F	0.7	A
Forward current surge peak	I _{FSM}	3.0	A 60HZ / 1CYC.
Junction temperature	T _j	150	°C

< MOSFET AND Di >

Total power dissipation	P _D	1.0	W/TOTAL/MOUNTED ON A CERAMIC BOARD
Range of storage temperature	T _{stg}	−55 to 150	°C

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●Electrical characteristics (Ta=25°C)

<MOSFET>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	±10	μA	V _{GS} =±12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	–20	–	–	V	I _D =–1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	–1	μA	V _{DS} =–20V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	–0.7	–	–2.0	V	V _{DS} =–10V, I _D =–1mA
Static drain-source on-starte resistance	R _{DS (on)} *	–	280	390	mΩ	I _D =–1A, V _{GS} =–4.5V
		–	310	430	mΩ	I _D =–1A, V _{GS} =–4V
		–	570	800	mΩ	I _D =–0.5A, V _{GS} =–2.5V
Forward transfer admittance	Y _{fs} *	0.7	–	–	S	V _{DS} =–10V, I _D =–0.5A
Input capacitance	C _{iss}	–	150	–	pF	V _{DS} =–10V
Output capacitance	C _{oss}	–	20	–	pF	V _{GS} =0V
Reverse transfer capacitance	C _{riss}	–	20	–	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	–	9	–	ns	I _D =–0.5A V _{DD} =–15V
Rise time	t _r *	–	8	–	ns	V _{GS} =–4.5V
Turn-off delay time	t _{d (off)} *	–	25	–	ns	R _L =30Ω
Fall time	t _f *	–	10	–	ns	R _G =10Ω
Total gate charge	Q _g	–	2.1	–	nC	V _{DD} =–15V V _{GS} =–5V
Gate-source charge	Q _{gs}	–	0.5	–	nC	I _D =–1A
Gate-drain charge	Q _{gd}	–	0.5	–	nC	R _L =15Ω R _G =10Ω

* Pulsed

<MOSFET>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	–	–	–1.2	V	I _S =–0.4A, V _{GS} =0V

<Di>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage drop	V _F	–	–	0.49	V	I _F =0.7A
Reverse leakage	I _R	–	–	200	μA	V _R =20V

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●Electrical characteristic curves

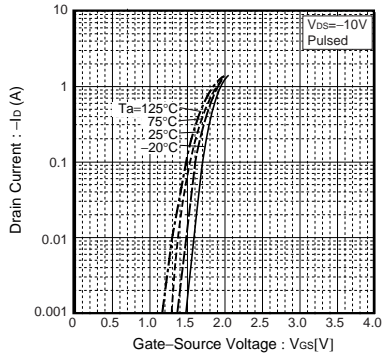


Fig.1 Typical Transfer Characteristics

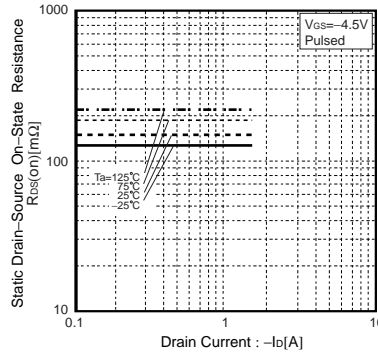


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

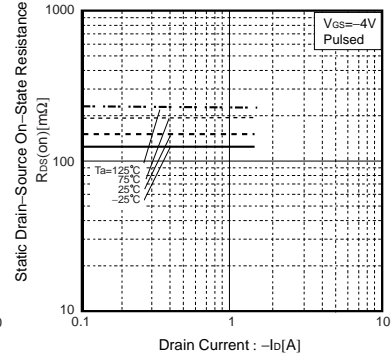


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

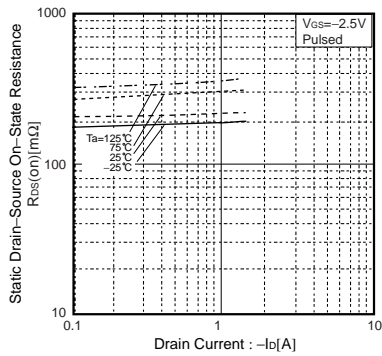


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

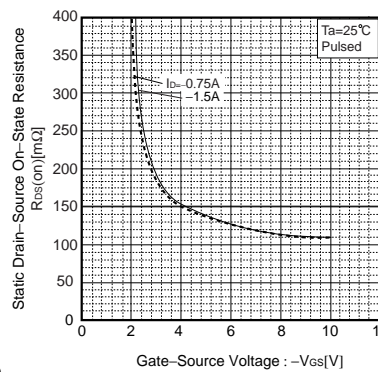


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

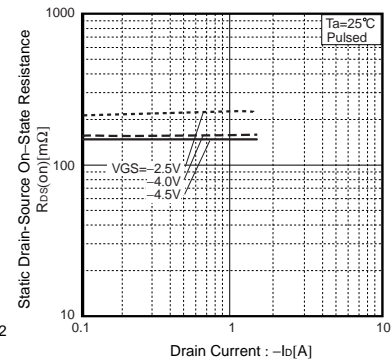


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

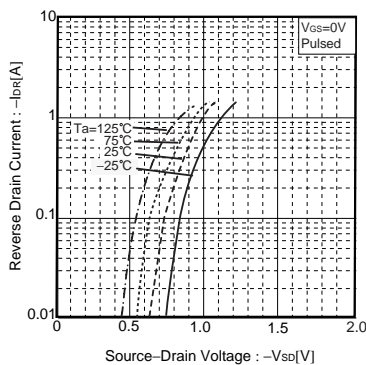


Fig.7 Reverse Drain Current vs. Source-Drain Current

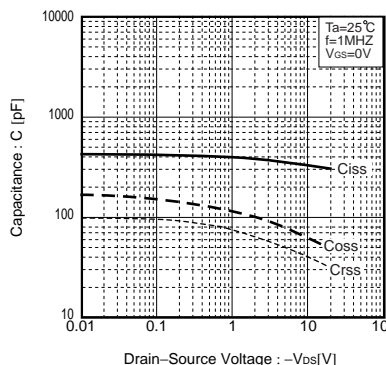


Fig.8 Typical Capacitance vs. Drain-Source Voltage

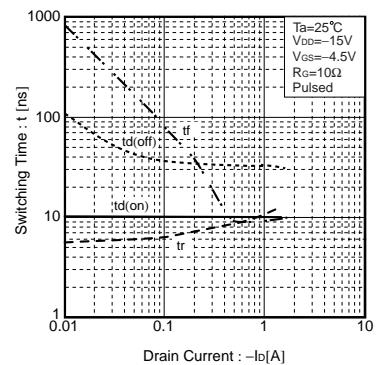


Fig.9 Switching Characteristics

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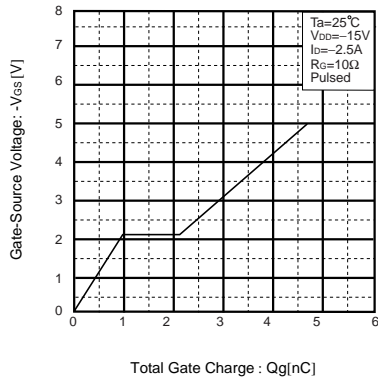


Fig.10 Dynamic Input Characteristics

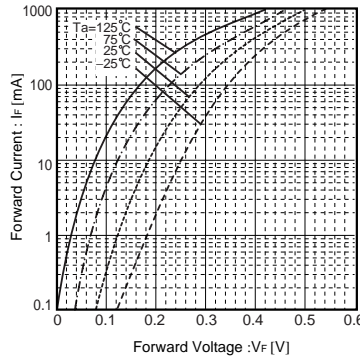


Fig.11 Forward Temperature Characteristics

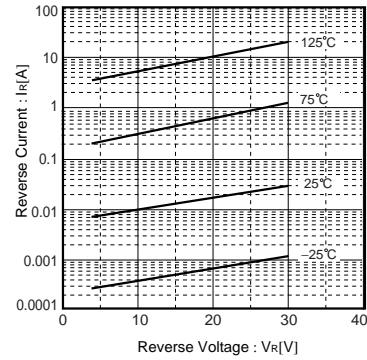


Fig.12 Reverse Temperature Characteristics

●Measurement circuits

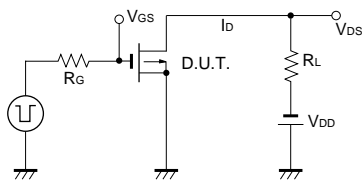


Fig.13 Switching Time Measurement Circuit

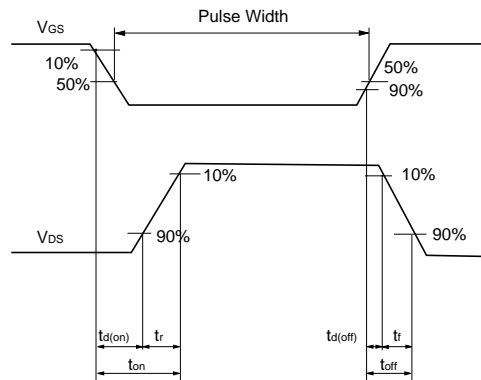


Fig.14 Switching Waveforms

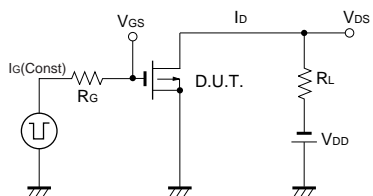


Fig.15 Gate Charge Measurement Circuit

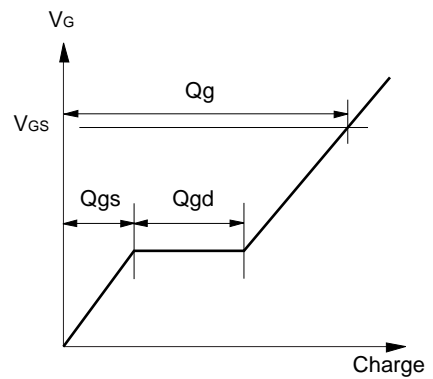


Fig.16 Gate Charge Waveforms

Appendix

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